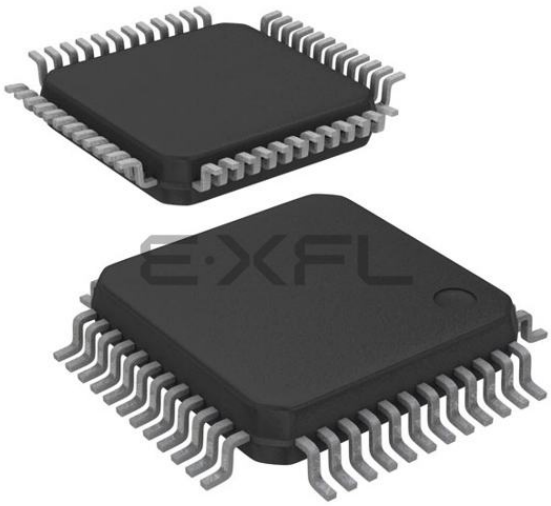
Renesas Electronics America Inc - R7FS124773A01CFL#AA0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, I²C, SCI, SPI, UART/USART, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	35
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 14x14b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs124773a01cfl-aa0

1. Overview

The MCU integrates multiple series of software- and pin-compatible Arm®-based 32-bit MCUs that share a common set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

Based on the energy-efficient Arm Cortex®-M0+ core, the MCU is particularly well suited for cost-sensitive and low-power applications with the following features:

- 128-KB code flash memory
- 16-KB SRAM
- Capacitive Touch Sensing Unit (CTSU)
- 14-bit A/D Converter (ADC14)
- 12-bit D/A Converter (DAC12)
- Security features.

1.1 Function Outline

Table 1.1 Arm core

Feature	Functional description
Arm Cortex-M0+	• Maximum operating frequency: up to 32 MHz • Arm Cortex-M0+: - Revision: r0p1-00rel0 - Armv6-M architecture profile - Single-cycle integer multiplier. • SysTick timer - Driven by SYSTICCLK (LOCO) or ICLK.

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 128 KB code flash memory. See section 37, Flash Memory in User's Manual.
Data flash memory	4 KB data flash memory. See section 37, Flash Memory in User's Manual.
Option-setting memory	The option-setting memory determines the state of the MCU after a reset. See section 6, Option-Setting Memory in User's Manual.
SRAM	On-chip high-speed SRAM with even parity bit. See section 36, SRAM in User's Manual.

Table 1.3 System (1 of 2)

Feature	Functional description
Operating mode	Two operating modes: • Single-chip mode • SCI boot mode. See section 3, Operating Modes in User's Manual.
Reset	9 types of resets: • RES pin reset • Power-on reset • Independent watchdog timer reset • Watchdog timer reset • Voltage monitor 0 reset • Voltage monitor 1 reset • Voltage monitor 2 reset • SRAM parity error reset • Software reset. See section 5, Resets in User's Manual.
Low Voltage Detection (LVD)	The Low Voltage Detection (LVD) monitors the voltage level input to the VCC pin and the detection level can be selected using a software program. See section 7, Low Voltage Detection (LVD) in User's Manual.

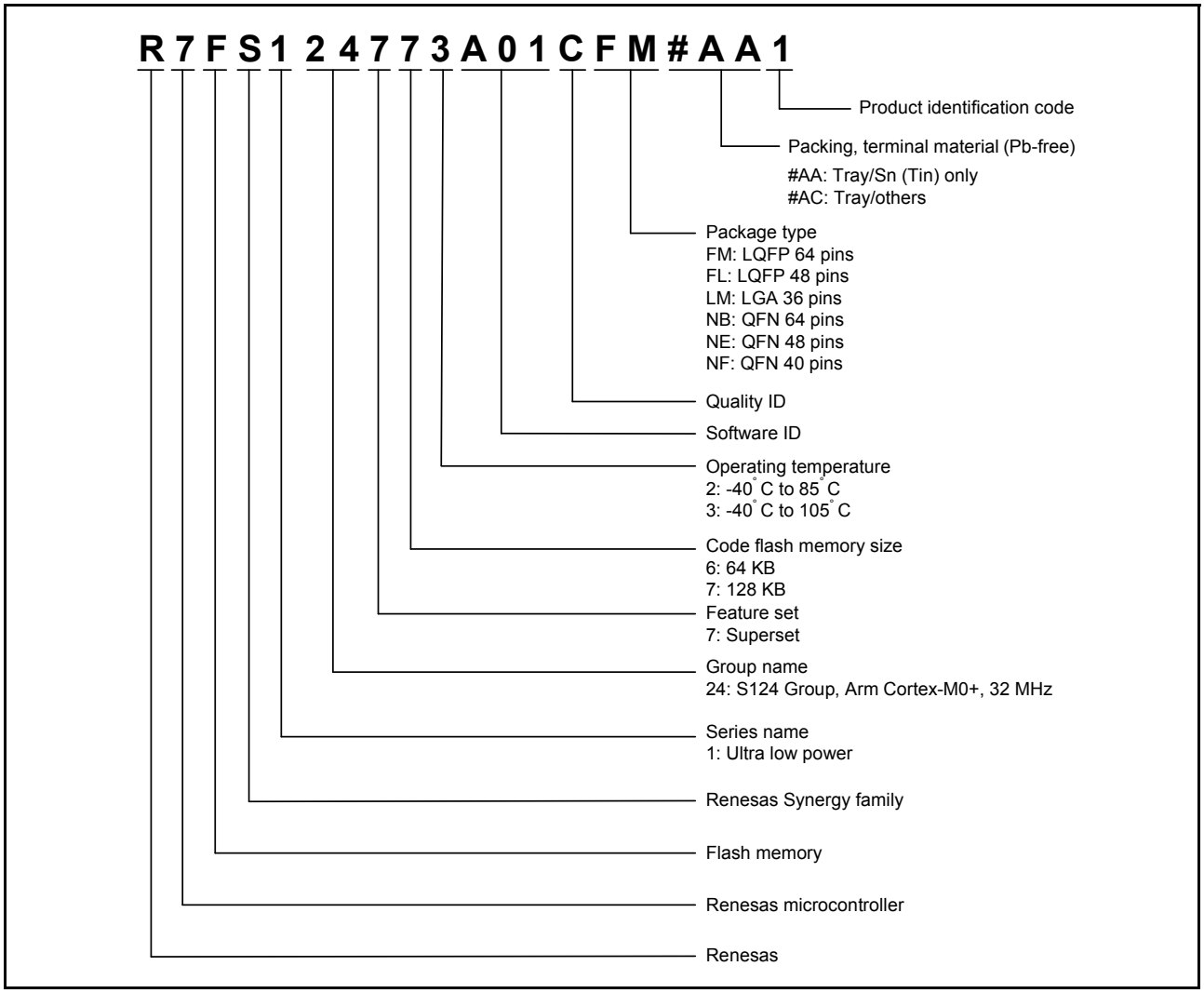


Figure 1.2 Part numbering scheme

Table 1.12 Product list

Product part number	Orderable part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FS124773A01CFM	R7FS124773A01CFM#AA1	PLQP0064KB-C	128 KB	4 KB	16 KB	–40 to +105°C
R7FS124773A01CNB	R7FS124773A01CNB#AC1	PWQN0064LA-A				–40 to +105°C
R7FS124773A01CFL	R7FS124773A01CFL#AA1	PLQP0048KB-B				–40 to +105°C
R7FS124773A01CNE	R7FS124773A01CNE#AC1	PWQN0048KB-A				–40 to +105°C
R7FS124773A01CNF	R7FS124773A01CNF#AC1	PWQN0040KC-A				–40 to +105°C
R7FS124772A01CLM	R7FS124772A01CLM#AC1	PWLG0036KA-A				–40 to +85°C
R7FS124763A01CFM	R7FS124763A01CFM#AA1	PLQP0064KB-C	64 KB			–40 to +105°C
R7FS124763A01CFL	R7FS124763A01CFL#AA1	PLQP0048KB-B				–40 to +105°C
R7FS124762A01CLM	R7FS124762A01CLM#AC1	PWLG0036KA-A				–40 to +85°C

Note: Earlier products with orderable part number suffix AA0 and AC0 have a restriction in AES functions. If AES functions are required for your application, refer to the products with orderable part number suffix AA1 or AC1. For details on the differences of AES functions between AA0/AC0 and AA1/AC1 products, see *Technical Update (TN-SY*-A024A/E)*. Contact your Renesas sales representative for additional information.

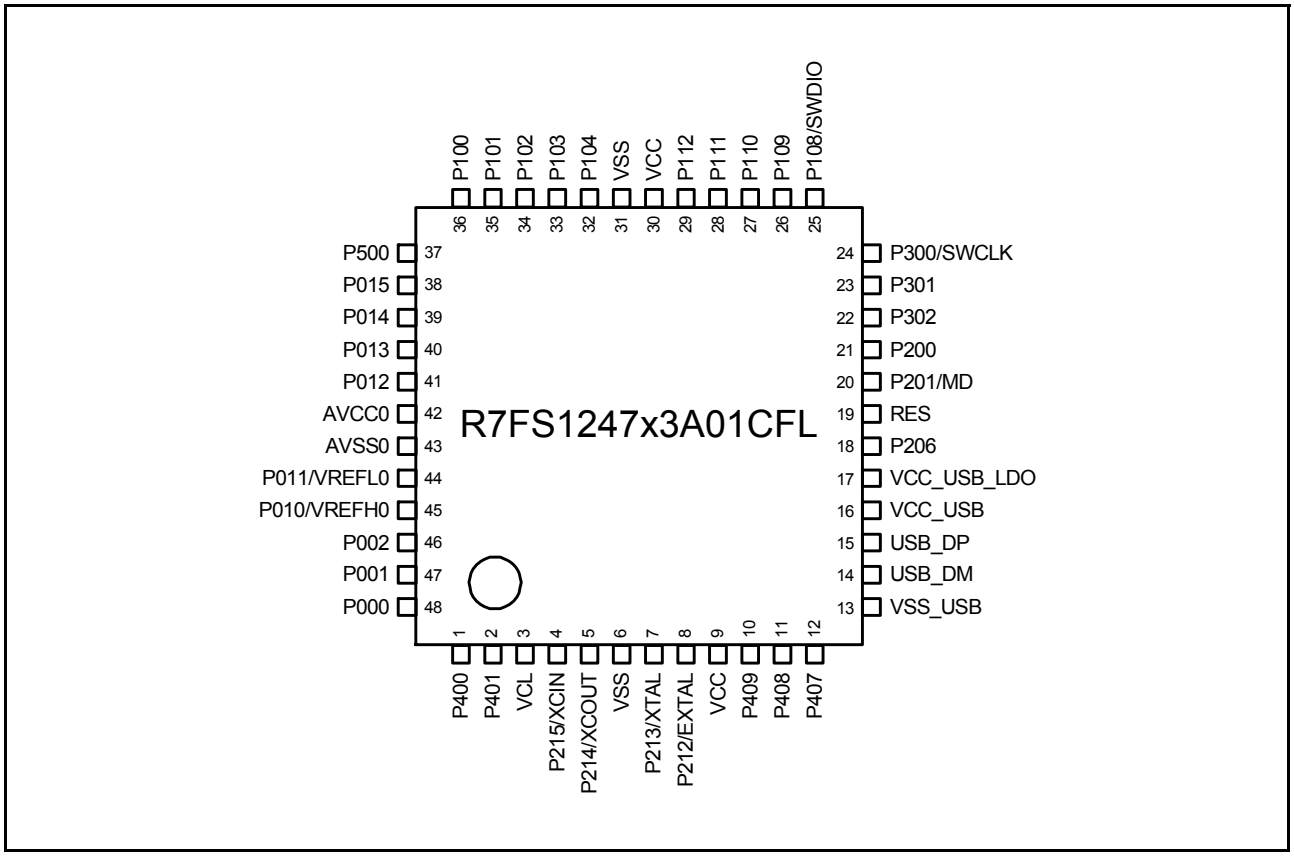


Figure 1.5 Pin assignment for LQFP 48-pin (top view)

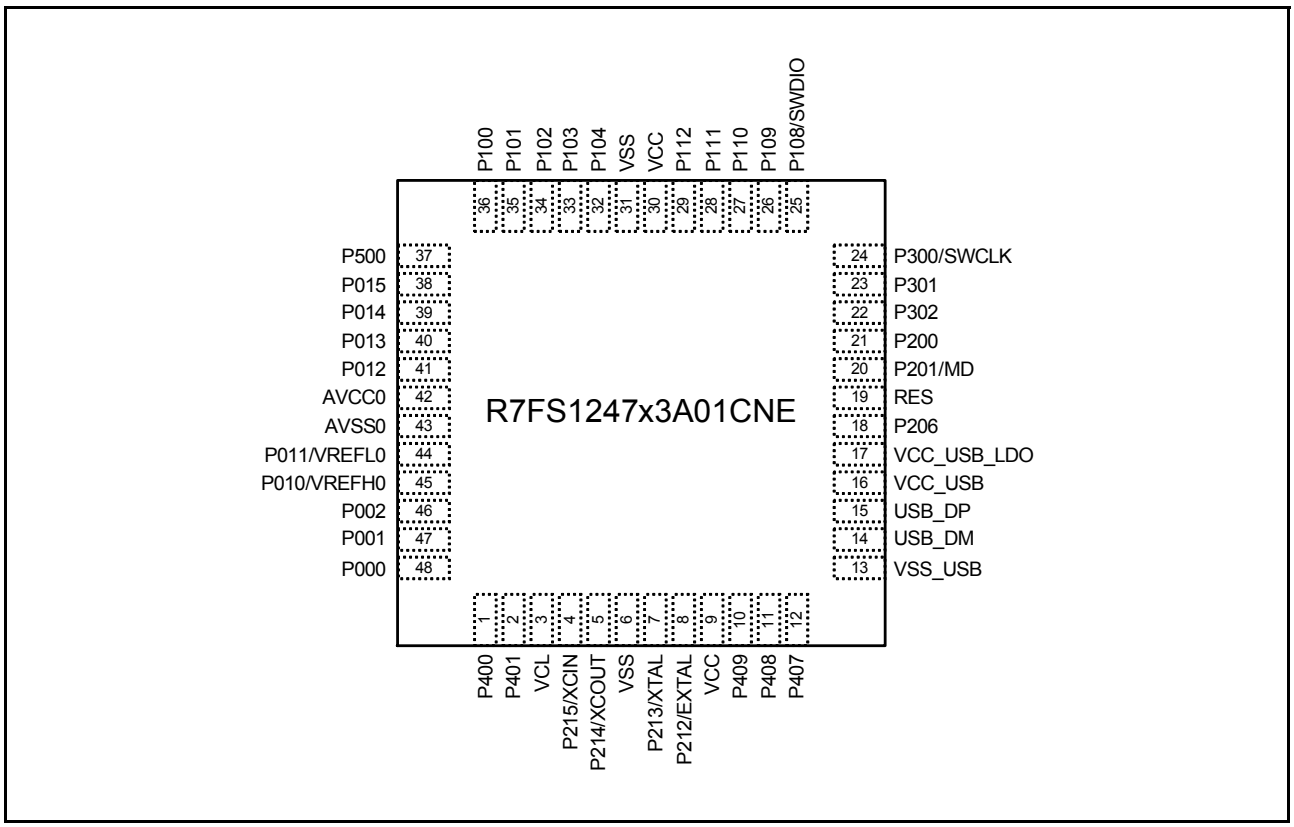


Figure 1.6 Pin assignment for QFN 48-pin (top view)

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

VCC*1 = AVCC0 = VCC_USB*2 = VCC_USB_LDO*2 = 1.6 to 5.5V, VREFH0 = 1.6 to AVCC0,

VSS = AVSS0 = VREFL0 = VSS_USB = 0 V, Ta = T_{opr}

Note 1. The typical condition is set to VCC = 3.3V.
Note 2. When USBFS is not used.

Figure 2.1 shows the timing conditions.

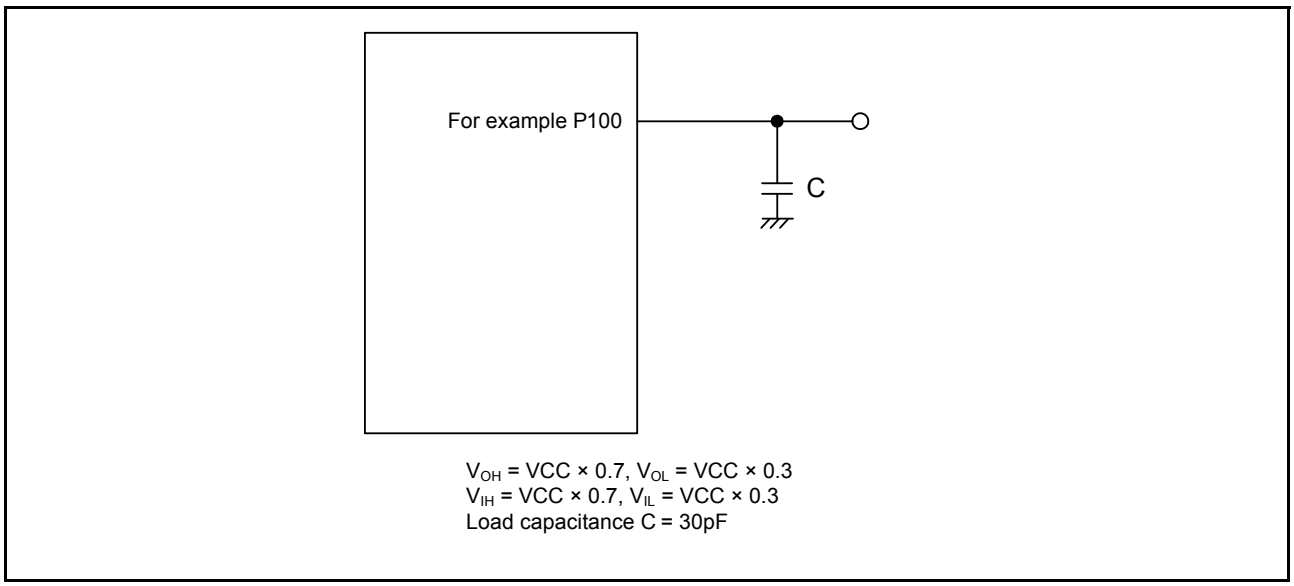


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation. However, make sure to adjust driving abilities of each pins to meet your conditions.

Each function pin used for the same function must select the same drive ability. If I/O drive ability of each function is mixed, the AC specification of the function is not guaranteed.

2.2.7 P408, P409 I/O Pin Output Characteristics of Middle Drive Capacity

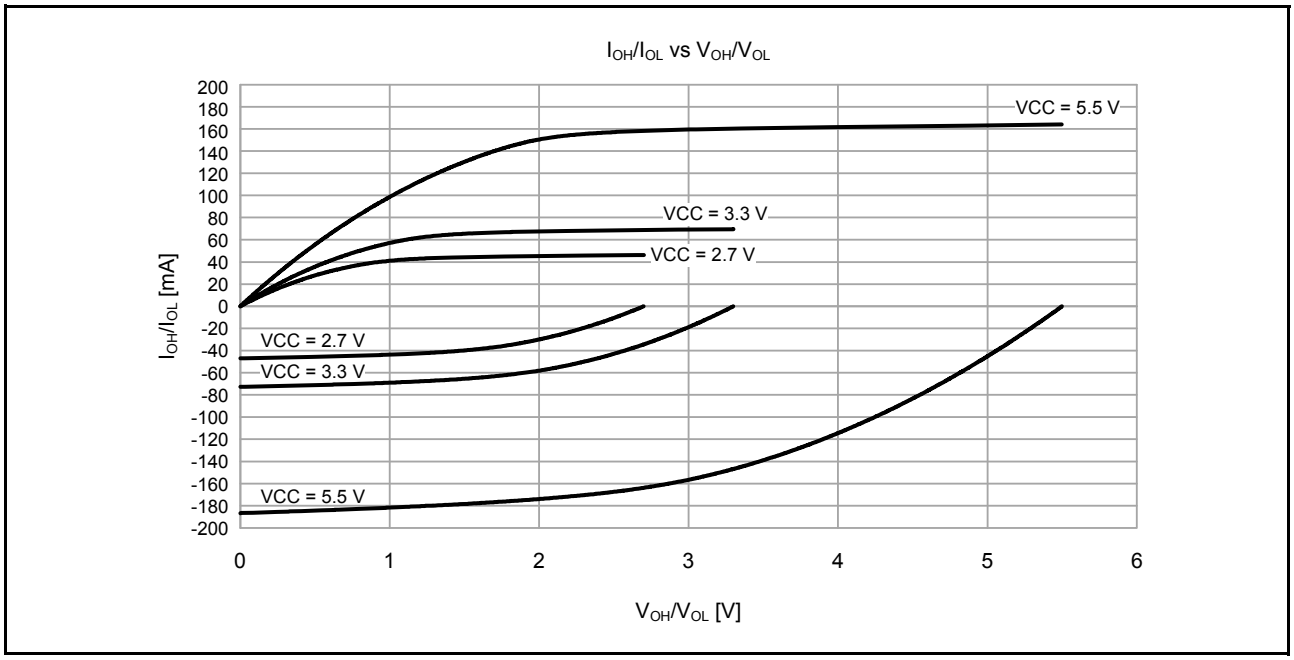


Figure 2.12 **V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C when middle drive output is selected (reference data)**

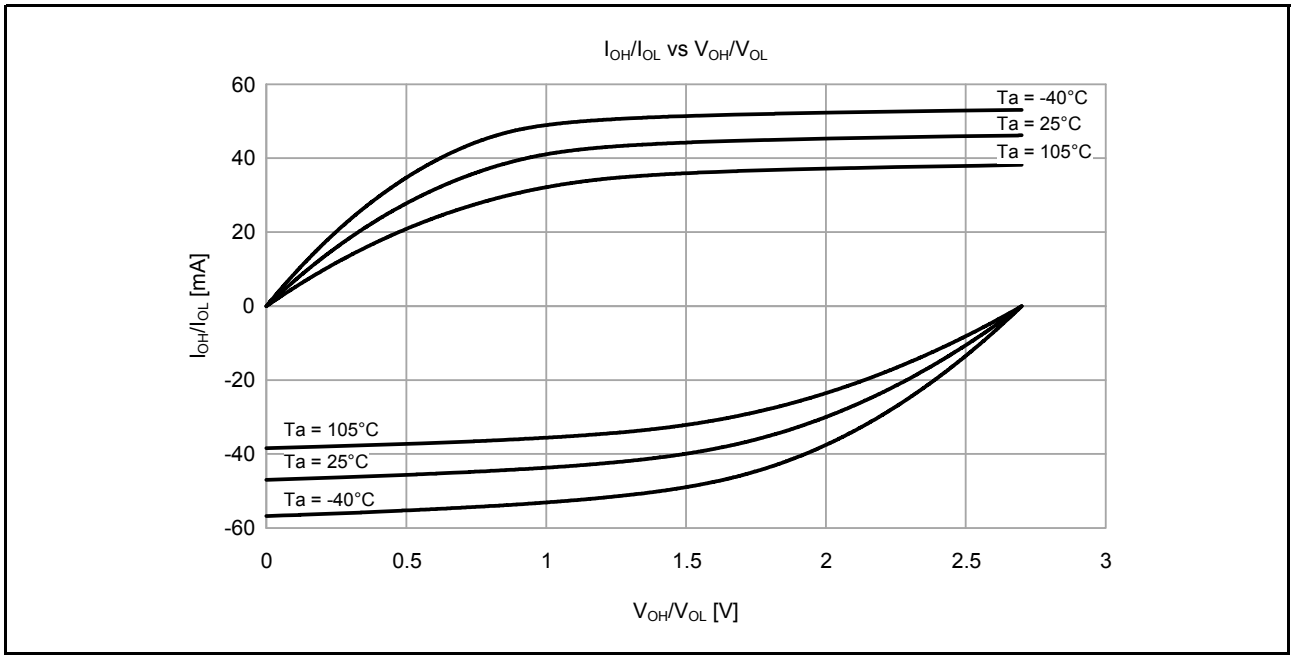
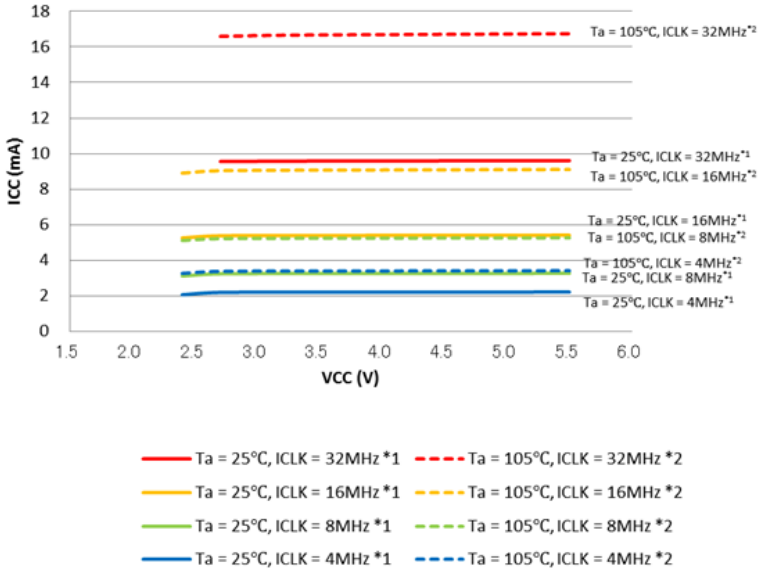


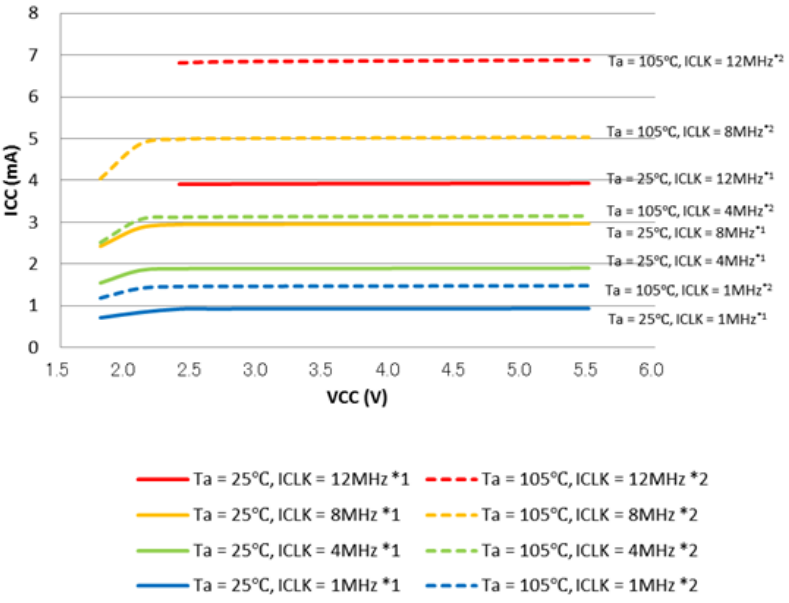
Figure 2.13 **V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 2.7 V when middle drive output is selected (reference data)**



Note 1. All peripheral operations except any BGO operation are operating normally. This is the average of the actual measurements of the sample cores during product evaluation.

Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the actual measurements for the upper limit samples during product evaluation.

Figure 2.17 Voltage dependency in high-speed operating mode (reference data)



Note 1. All peripheral operations except any BGO operation are operating normally. This is the average of the actual measurements of the sample cores during product evaluation.

Note 2. All peripheral operations except any BGO operation are operating at maximum. This is the average of the actual measurements for the upper limit samples during product evaluation.

Figure 2.18 Voltage dependency in middle-speed operating mode (reference data)

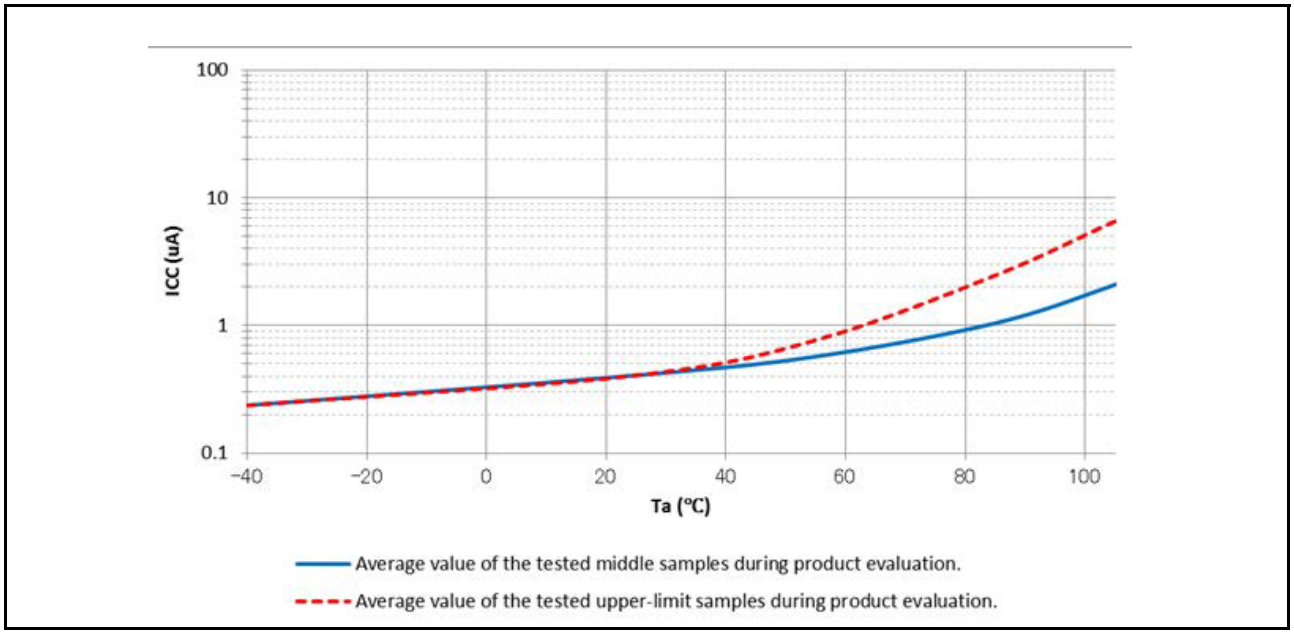


Figure 2.22 Temperature dependency in Software Standby mode (reference data)

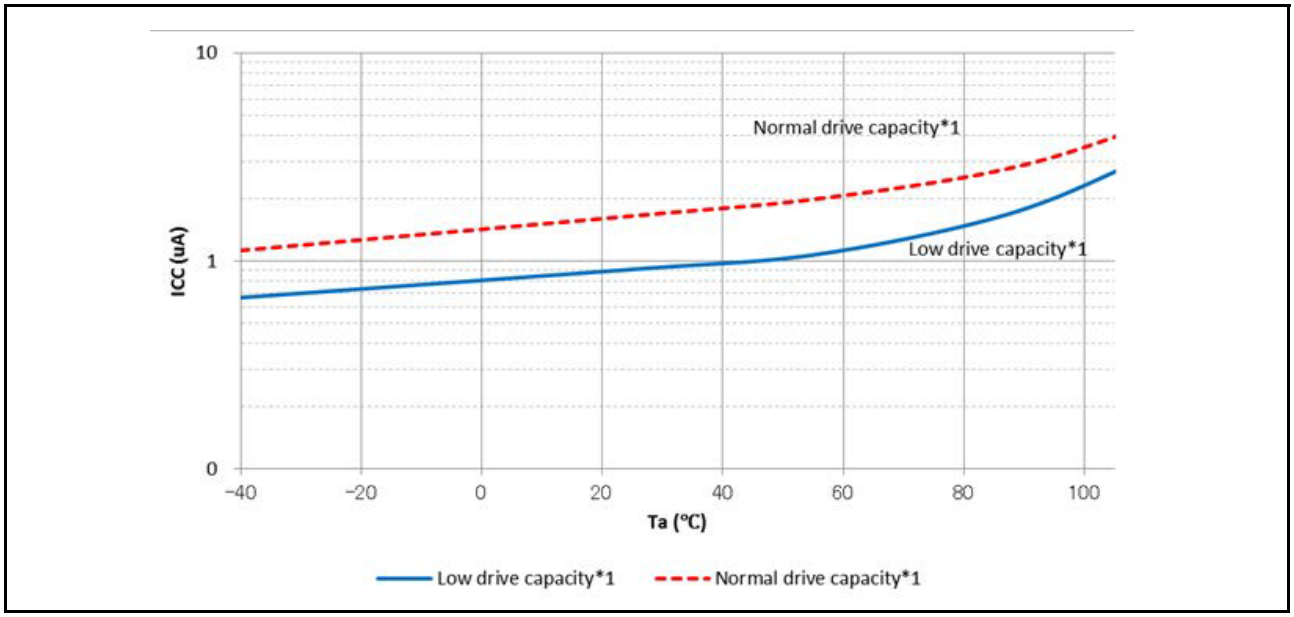


Figure 2.23 Temperature dependency of RTC operation (reference data)

Table 2.13 Operating and standby current (3) (1 of 2)

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Analog power supply current	During A/D conversion (at high-speed conversion)	I_{AVCC}	-	-	3.0	mA	-
	During A/D conversion (at low-power conversion)		-	-	1.0	mA	-
	During D/A conversion*1		-	0.4	0.8	mA	-
	Waiting for A/D and D/A conversion (all units)*5		-	-	1.0	µA	-
Reference power supply current	During A/D conversion	I_{REFH0}	-	-	150	µA	-
	Waiting for A/D conversion (all units)		-	-	60	nA	-
Temperature sensor		I_{TNS}	-	75	-	µA	-

2.3.5 NMI and IRQ Noise Filter

Table 2.29 NMI and IRQ noise filter

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
NMI pulse width	t_{NMIW}	200	-	-	ns	NMI digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		NMI digital filter enabled	$t_{NMICK} \times 3 \leq 200$ ns
		$t_{NMICK} \times 3.5$*2	-	-			$t_{NMICK} \times 3 > 200$ ns
IRQ pulse width	t_{IRQW}	200	-	-	ns	IRQ digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		IRQ digital filter enabled	$t_{IRQCK} \times 3 \leq 200$ ns
		$t_{IRQCK} \times 3.5$*3	-	-			$t_{IRQCK} \times 3 > 200$ ns

Note: 200 ns minimum in Software Standby mode.
Note 1. t_{Pcyc} indicates the PCLKB cycle.
Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.
Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 7).

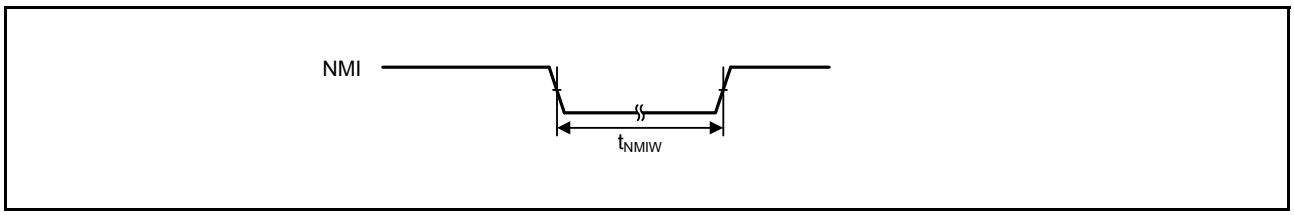


Figure 2.33 NMI interrupt input timing

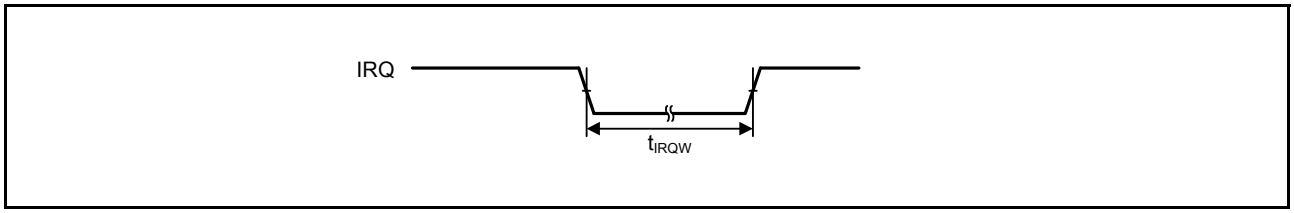


Figure 2.34 IRQ interrupt input timing

2.3.6 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 Trigger Timing

Table 2.30 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 trigger timing

Parameter			Symbol	Min	Max	Unit	Test conditions
I/O Ports	Input data pulse width		t_{PRW}	1.5	-	t_{Pcyc}	Figure 2.35
POEG	POEG input trigger pulse width		t_{POEW}	3	-	t_{Pcyc}	Figure 2.36
GPT	Input capture pulse width	Single edge	t_{GTICW}	1.5	-	t_{PDcyc}	Figure 2.37
		Dual edge		2.5	-		
AGT	AGTIO, AGTEE input cycle	2.7 V ≤ VCC ≤ 5.5 V	t_{ACYC}*1	250	-	ns	Figure 2.38
		2.4 V ≤ VCC < 2.7 V		500	-	ns	
		1.8 V ≤ VCC < 2.4 V		1000	-	ns	
		1.6 V ≤ VCC < 1.8 V		2000	-	ns	
	AGTIO, AGTEE input high level width, low-level width	2.7 V ≤ VCC ≤ 5.5 V	t_{ACKWH}, t_{ACKWL}	100	-	ns	
		2.4 V ≤ VCC < 2.7 V		200	-	ns	
		1.8 V ≤ VCC < 2.4 V		400	-	ns	
		1.6 V ≤ VCC < 1.8 V		800	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB output cycle	2.7 V ≤ VCC ≤ 5.5 V	t_{ACYC2}	62.5	-	ns	Figure 2.38
		2.4 V ≤ VCC < 2.7 V		125	-	ns	
		1.8 V ≤ VCC < 2.4 V		250	-	ns	
		1.6 V ≤ VCC < 1.8 V		500	-	ns	
ADC14	14-bit A/D converter trigger input pulse width		t_{TRGW}	1.5	-	t_{Pcyc}	Figure 2.39
KINT	KRn (n = 00 to 07) pulse width		t_{KR}	250	-	ns	Figure 2.40

Note: tPcyc: PCLKB cycle, tPDcyc: PCLKD cycle.
Note 1. Constraints on AGTIO input: t_{Pcyc} × 2 (t_{Pcyc}: PCLKB cycle) < t_{ACYC}.

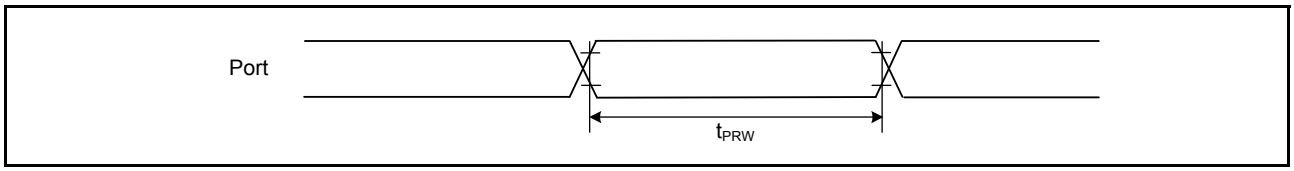


Figure 2.35 I/O ports input timing

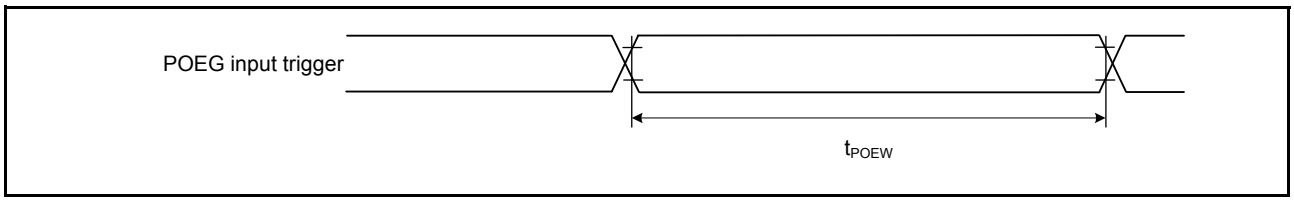


Figure 2.36 POEG input trigger timing

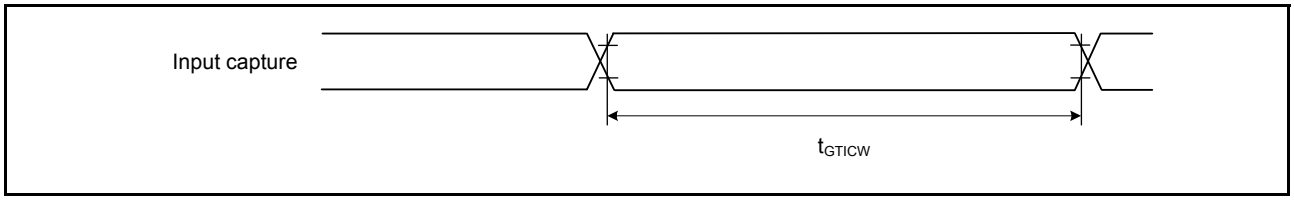


Figure 2.37 GPT input capture timing

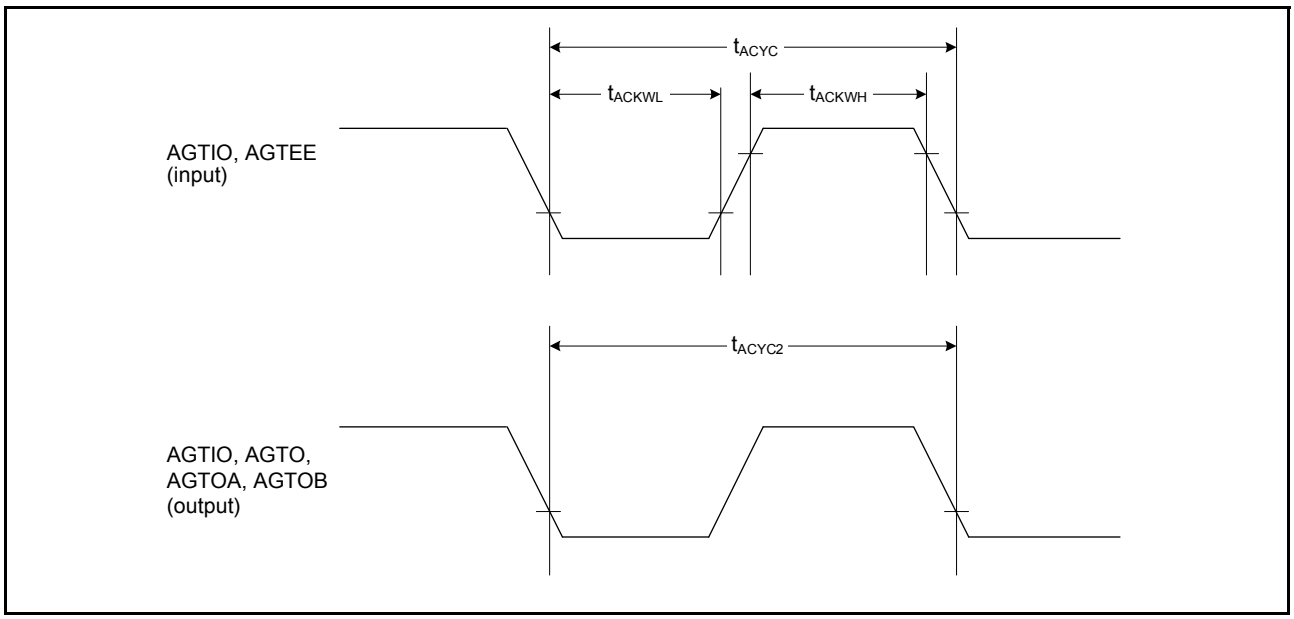


Figure 2.38 AGT I/O timing

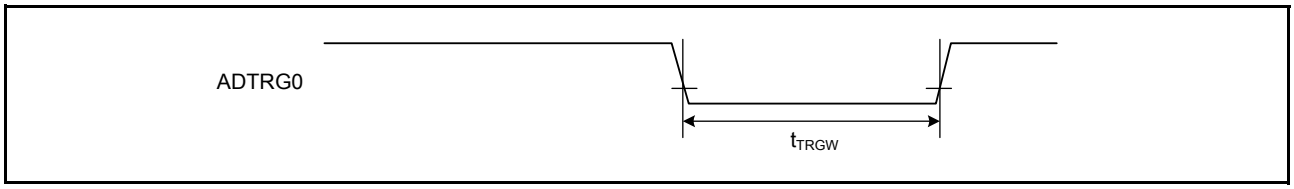


Figure 2.39 ADC14 trigger input timing

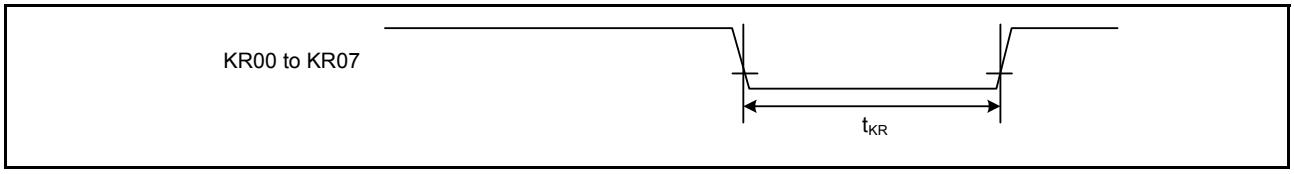


Figure 2.40 Key interrupt input timing

2.3.7 CAC Timing

Table 2.31 CAC timing

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
CAC	CACREF input pulse width	$t_{PBcyc} \leq tcac$*2	t_{CACREF}	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	-	ns	-
		$t_{PBcyc} > tcac$*2		$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	-	ns	

Note 1. t_{PBcyc}: PCLKB cycle.

Note 2. t_{cac}: CAC count clock source cycle.

2.3.8 SCI Timing

Table 2.32 SCI timing (1)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter				Symbol	Min	Max	Unit*1	Test conditions
SCI	Input clock cycle	Asynchronous		t_{Scyc}	4	-	t_{Pcyc}	Figure 2.41
		Clock synchronous			6	-		
	Input clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Input clock rise time			t_{SCKr}	-	20	ns	
	Input clock fall time			t_{SCKf}	-	20	ns	
	Output clock cycle	Asynchronous		t_{Scyc}	6	-	t_{Pcyc}	
		Clock synchronous			4	-		
	Output clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Output clock rise time		1.8V or above	t_{SCKr}	-	20	ns	
			1.6V or above		-	30		
	Output clock fall time		1.8V or above	t_{SCKf}	-	20	ns	
			1.6V or above		-	30		
	Transmit data delay (master)	Clock synchronous	1.8V or above	t_{TXD}	-	40	ns	Figure 2.42
			1.6V or above		-	45		
	Transmit data delay (slave)	Clock synchronous	2.7V or above		-	55	ns	
			2.4V or above		-	60		
			1.8V or above		-	100		
			1.6V or above		-	125		
	Receive data setup time (master)	Clock synchronous	2.7V or above	t_{RXS}	45	-	ns	
			2.4V or above		55	-		
			1.8V or above		90	-		
			1.6V or above		110	-		
	Receive data setup time (slave)	Clock synchronous	2.7V or above		40	-	ns	
			1.6V or above		45	-		
	Receive data hold time (master)	Clock synchronous		t_{RXH}	5	-	ns	
	Receive data hold time (slave)	Clock synchronous		t_{RXH}	40	-	ns	

Note 1. t_{Pcyc}: PCLKB cycle.

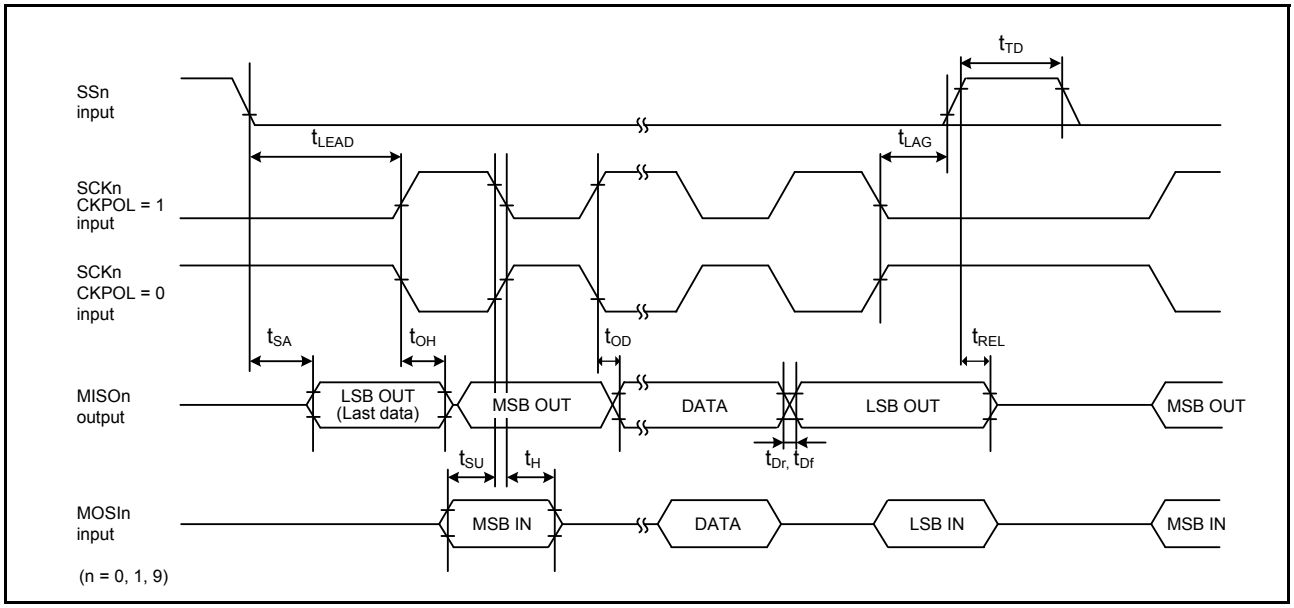


Figure 2.47 SCI simple SPI mode timing (slave, CKPH = 0)

Table 2.34 SCI timing (3)

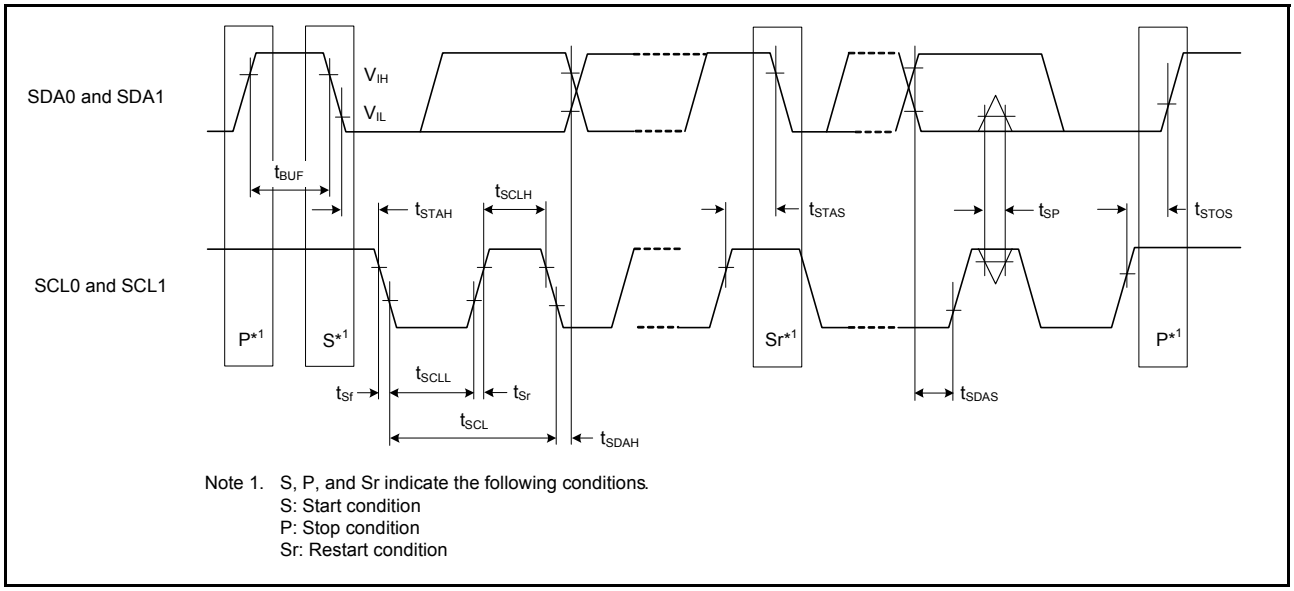
Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	Min	Max	Unit	Test conditions
Simple IIC (Standard mode)	SDA input rise time	t_{Sr}	-	1000	ns	Figure 2.48
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	4 × t_{IICcyc}	ns	
	Data input setup time	t_{SDAS}	250	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b*1	-	400	pF	
Simple IIC*2 (Fast mode)	SDA input rise time	t_{Sr}	-	300	ns	Figure 2.48
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	4 × t_{IICcyc}	ns	
	Data input setup time	t_{SDAS}	100	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b*1	-	400	pF	

Note: t_{IICcyc}: Clock cycle selected by the SMR.CKS[1:0] bits.

Note 1. Cb indicates the total capacity of the bus line.

Note 2. Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register.



Note 1. S, P, and Sr indicate the following conditions.
S: Start condition
P: Stop condition
Sr: Restart condition

Figure 2.56 I²C bus interface input/output timing

2.3.11 CLKOUT Timing

Table 2.37 CLKOUT timing

Parameter			Symbol	Min	Max	Unit*1	Test conditions
CLKOUT	CLKOUT pin output cycle*1	VCC = 2.7 V or above	t_{Ccyc}	62.5	-	ns	Figure 2.57
		VCC = 1.8 V or above		125	-		
		VCC = 1.6 V or above		250	-		
	CLKOUT pin high pulse width*2	VCC = 2.7 V or above	t_{CH}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin low pulse width*2	VCC = 2.7 V or above	t_{CL}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin output rise time	VCC = 2.7 V or above	t_{Cr}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		
	CLKOUT pin output fall time	VCC = 2.7 V or above	t_{Cf}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		

Note 1. When the EXTAL external clock input or an oscillator is used with division by 1 (the CKOCR.CKOSEL[2:0] bits are 011b and the CKOCR.CKODIV[2:0] bits are 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.

Note 2. When the MOCO is selected as the clock output source (the CKOCR.CKOSEL[2:0] bits are 001b), set the clock output division ratio selection to be divided by 2 (the CKOCR.CKODIV[2:0] bits are 001b).

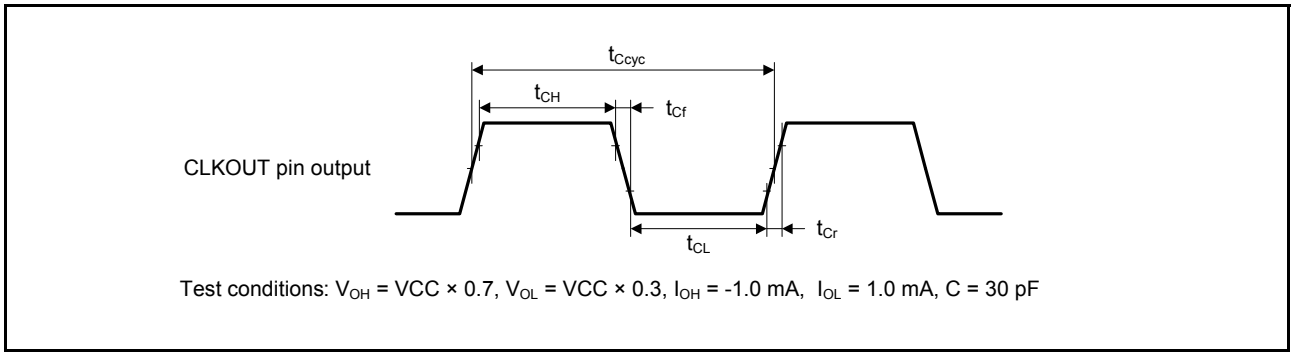


Figure 2.57 CLKOUT output timing

2.5 ADC14 Characteristics

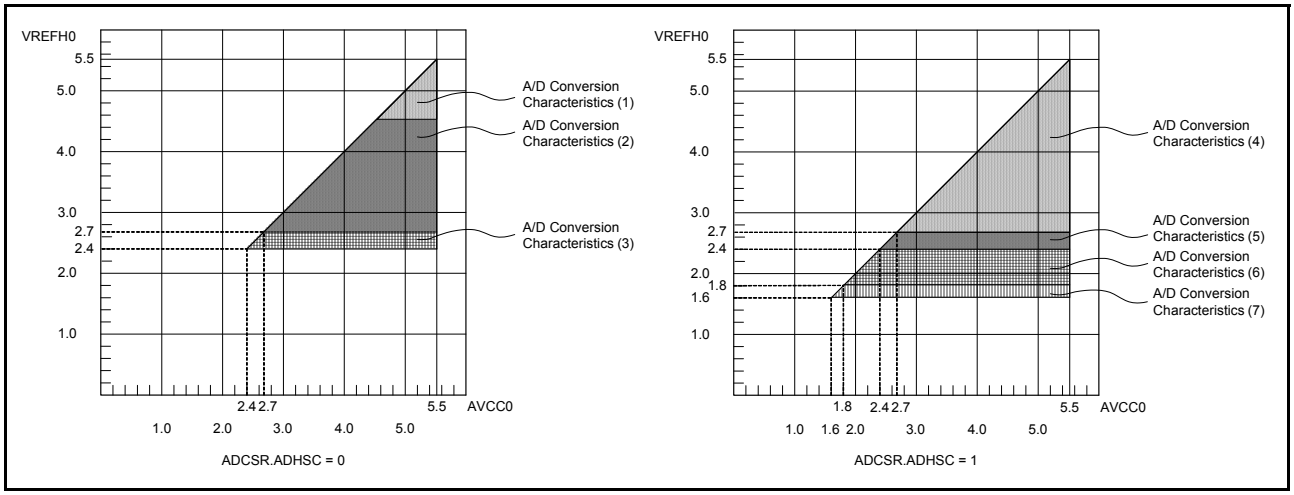


Figure 2.61 AVCC0 to VREFH0 voltage range

Table 2.40 A/D conversion characteristics (1) in high-speed A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 4.5 to 5.5 V, VREFH0 = 4.5 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	64	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	2.5*3	kΩ	High-precision channel
		-	-	6.7*3	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKD = 64 MHz)	Permissible signal source impedance Max. = 0.3 kΩ	0.70	-	-	µs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		1.13	-	-	µs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-

Table 2.44 A/D conversion characteristics (5) in low-power A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 16 MHz)	Permissible signal source impedance Max. = 2.2 kΩ	3.75	-	-	µs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		5.44	-	-	µs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

Table 2.45 A/D conversion characteristics (6) in low-power A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V, VSS = AVSS0 = VREFL0 = 0 V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	8	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	3.8*3	kΩ	High-precision channel
		-	-	8.2*3	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-

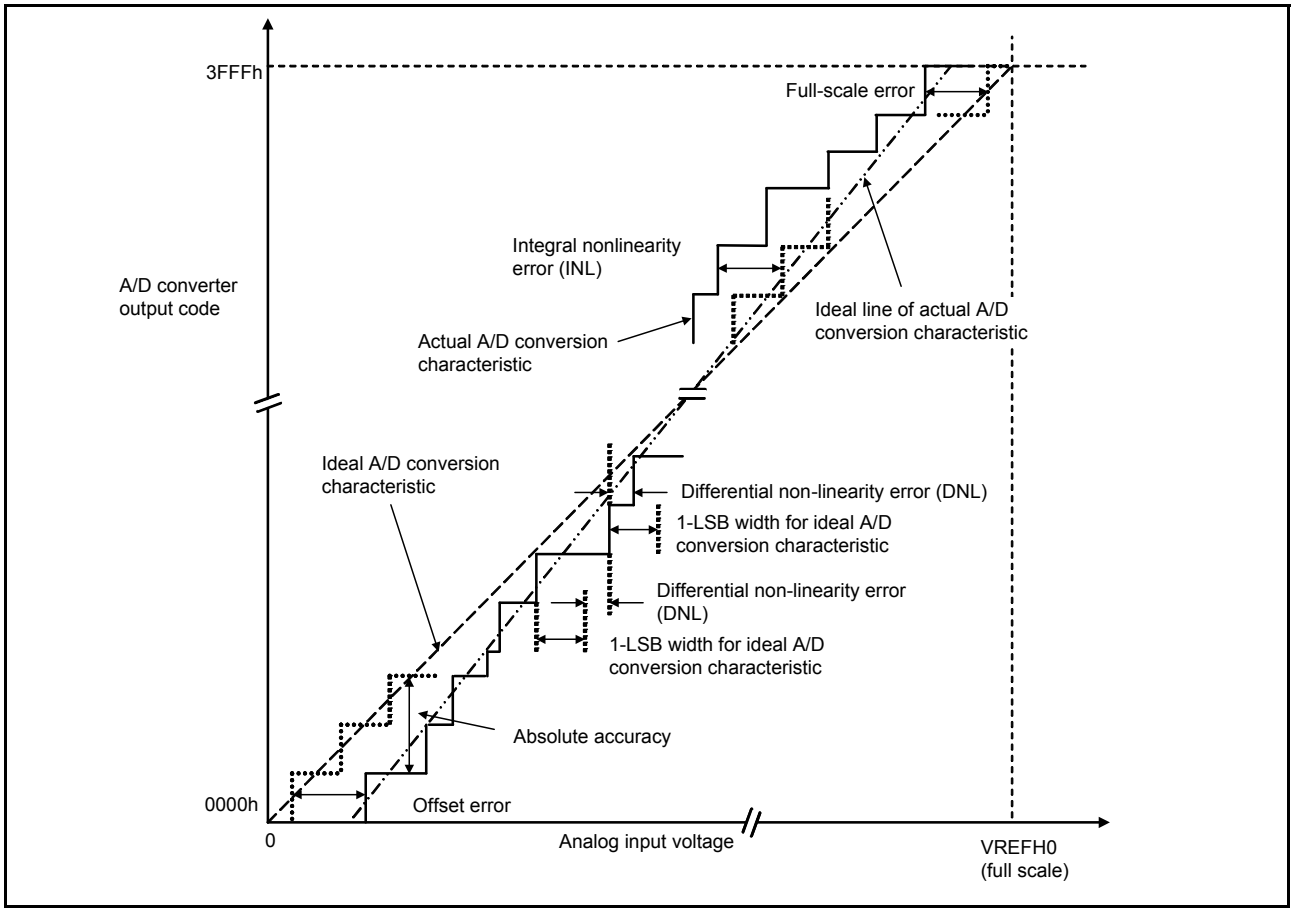


Figure 2.63 Illustration of 14-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ±5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

2.12 Flash Memory Characteristics

2.12.1 Code Flash Memory Characteristics

Table 2.56 Code flash characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N_{PEC}	1000	-	-	Times	-
Data hold time	After 1000 times N_{PEC}	t_{DRP}	20*2, *3	-	-	Year	T_a = +85°C

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be performed n times for each block. For instance, when 4-byte programming is performed 256 times for different addresses in 1-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. This result is obtained from reliability testing.

Table 2.57 Code flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	ICLK = 1 MHz			ICLK = 32 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	4-byte	t_{P4}	-	116	998	-	54	506	µs
Erasure time	1-KB	t_{E1K}	-	9.03	287	-	5.67	222	ms
Blank check time	4-byte	t_{BC4}	-	-	56.8	-	-	16.6	µs
	1-KB	t_{BC1K}	-	-	1899	-	-	140	µs
Erase suspended time		t_{SED}	-	-	22.5	-	-	10.7	µs
Startup area switching setting time		t_{SAS}	-	21.9	585	-	12.1	447	ms
Access window time		t_{AWS}	-	21.9	585	-	12.1	447	ms
OCD/serial programmer ID setting time		t_{OSIS}	-	21.9	585	-	12.1	447	ms
Flash memory mode transition wait time 1		t_{DIS}	2	-	-	2	-	-	µs
Flash memory mode transition wait time 2		t_{MS}	5	-	-	5	-	-	µs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Table 2.60 Data flash characteristics (2)
High-speed operating mode
Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	ICLK = 4 MHz			ICLK = 32 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	1-byte	t_{DP1}	-	52.4	463	-	42.1	387	µs
Erasure time	1-KB	t_{DE1K}	-	8.98	286	-	6.42	237	ms
Blank check time	1-byte	t_{DBC1}	-	-	24.3	-	-	16.6	µs
	1-KB	t_{DBC1K}	-	-	1872	-	-	512	µs
Suspended time during erasing		t_{DSED}	-	-	13.0	-	-	10.7	µs
Data flash STOP recovery time		t_{DSTOP}	5	-	-	5	-	-	µs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Table 2.61 Data flash characteristics (3)
Middle-speed operating mode
Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter		Symbol	ICLK = 4 MHz			ICLK = 8 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	1-byte	t_{DP1}	-	94.7	886	-	89.3	849	µs
Erasure time	1-KB	t_{DE1K}	-	9.59	299	-	8.29	273	ms
Blank check time	1-byte	t_{DBC1}	-	-	56.2	-	-	52.5	µs
	1-KB	t_{DBC1K}	-	-	2.17	-	-	1.51	ms
Suspended time during erasing		t_{DSED}	-	-	23.0	-	-	21.7	µs
Data flash STOP recovery time		t_{DSTOP}	720	-	-	720	-	-	ns

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

General Precautions

1. Precaution against Electrostatic Discharge (ESD)

   A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

   The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

   Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

   Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

   After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

   Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

   Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

   Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.